

300-MHz Quadrature Modulator

Description

The IC U2793B is a 300-MHz quadrature modulator that uses Atmel Wireless & Microcontrollers' advanced UHF process. It features low current consumption, single-ended RF ports and adjustment-free application, which makes the device suitable for all digital radio systems, e.g., GSM, PCN, JDC and WLAN. As an option, output level and spurious products are adjustable at Pins 19

and 20. In conjunction with Atmel Wireless & Microcontrollers' U2795B mixer, an up converter up to 2 GHz can be realized.

Electrostatic sensitive device.
Observe precautions for handling.



Features

- Supply voltage: 5 V (typical)
- Low power consumption: 15 mA / 5 V (typical at 0 dBm output level)
- Output level and spurious products adjustable (optional)
- Excellent sideband suppression by means of duty cycle regeneration of the LO input signal
- Phase-control loop for precise 90° phase shifting
- Power-down mode
- Low LO input level: -15 dBm (typical)
- 50-Ω single-ended LO and RF port
- LO frequency range of 30 MHz to 300 MHz

Benefits

- Extended talk time due to increased battery life
- Few external components results in cost and board space saving
- Adjustment free hence saves time
- Modular system for different applications by adding U2795B reduces the costs

Block Diagram

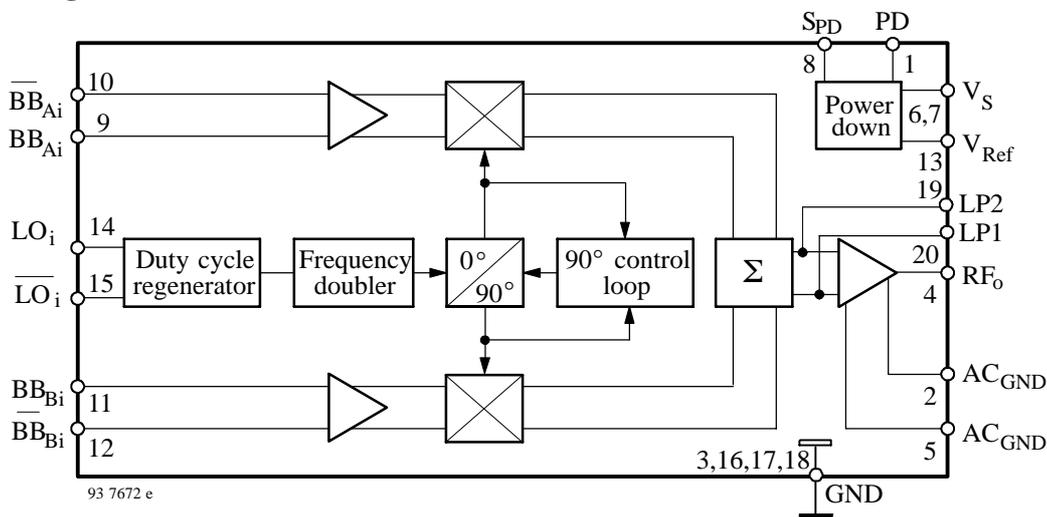


Figure 1. Block diagram

Ordering Information

Extended Type Number	Package	Remarks
U2793B-MFS	SSO20	Tube
U2793B-MFSG3	SSO20	Taped and reeled

Pin Description

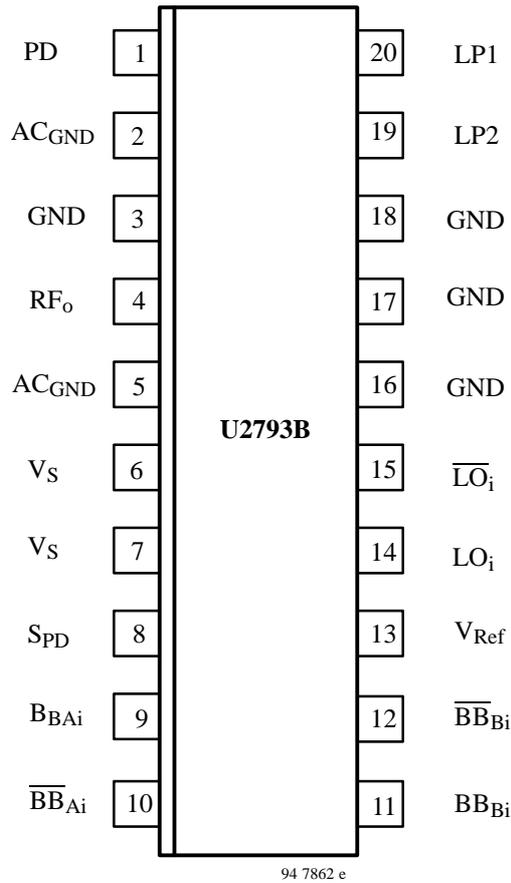


Figure 2. Pinning SSO20

Pin	Symbol	Function
1	PD	Power down port
2	AC _{GND}	AC ground
3	GND	Ground
4	RF _o	RF output
5	AC _{GND}	AC ground
6	V _S	Supply voltage
7	V _S	Supply voltage
8	S _{PD}	Settling time power down
9	BB _{Ai}	Baseband input A
10	$\overline{\text{BB}}_{\text{Ai}}$	Baseband input A inverse
11	BB _{Bi}	Baseband input B
12	$\overline{\text{BB}}_{\text{Bi}}$	Baseband input B inverse
13	V _{Ref}	Reference voltage (2.5 V)
14	LO _i	Input LO
15	$\overline{\text{LO}}_{\text{i}}$	Input LO inverse, typically grounded
16	GND	Ground
17	GND	Ground
18	GND	Ground
19	LP2	Output low pass and power control
20	LP1	Output low pass and power control

Absolute Maximum Ratings

Parameters	Symbol	Value	Unit
Supply voltage Pins 6 and 7	V _S	6	V
Input voltage Pins 9, 10, 11, 12, 14 and 15	V _i	0 to V _S	V
Junction temperature	T _j	125	°C
Storage temperature range	T _{stg}	-40 to +125	°C

Operating Range

Parameters	Symbol	Value	Unit
Supply voltage Pins 6 and 7	V _S	4.5 to 5.5	V
Ambient temperature range	T _{amb}	-40 to +85	°C

Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient SSO20	R _{thja}	140	K/W

Electrical Characteristics

Test conditions (unless otherwise specified); $V_S = 5\text{ V}$, $T_{\text{amb}} = 25^\circ\text{C}$, referred to test circuit.
System impedance $Z_o = 50\ \Omega$, $f_{\text{LO}} = 150\text{ MHz}$, $P_{\text{LO}} = -15\text{ dBm}$, $V_{\text{BBi}} = 1.0\text{ V}_{\text{pp}}$, differential

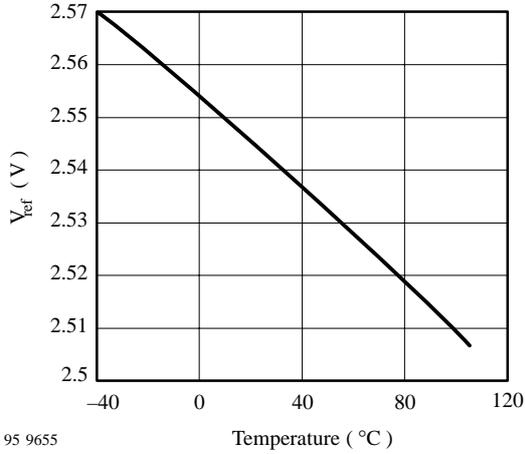
Parameters	Test conditions / Pin	Symbol	Min.	Typ.	Max.	Unit
Supply-voltage range	Pins 6 and 7	V_S	4.5	5	5.5	V
Supply current	Pins 6 and 7	I_S		15		mA
Baseband inputs Pin 9–10, 11–12						
Input-voltage range (diff.)		V_{BBi}		1000	1500	mV _{pp}
Input impedance		Z_{BBi}		30		k Ω
Input-frequency range		f_{BBi}	0		50	MHz
LO input Pins 14 and 15						
Frequency range		f_{LOi}	30		300	MHz
Input level ¹		P_{LOi}		-15	-5	dBm
Input impedance		Z_{iLO}		2)		Ω
Voltage standing wave ratio		VSWR_{LO}		3.5		
Duty-cycle range		DCR_{LO}	0.4		0.6	
RF output Pin 4						
Output level	$f_{\text{LO}} = 150\text{ MHz}$, $V_{\text{BBi}} = 1\text{ V}_{\text{pp}}$, differential $f_{\text{LO}} = 50\text{ MHz}$, $V_{\text{BBi}} = 0.3\text{ V}_{\text{pp}}$, differential	P_{RFo}	-3	-1 0		dBm
LO suppression	$P_{\text{LO}} = -20\text{ dBm}$	LO_{RFo}	32	45		dB
Voltage standing wave ratio		VSWR_{RF}		1.4	2	
Sideband suppression ³		SBS_{RFo}	35	45		dB
Phase error ⁴		P_e		<1		deg
Amplitude error		A_e		< ± 0.25		dB
Noise floor	$V_{\text{BBi}} = 2\text{ V}$, $\overline{V_{\text{BBi}}} = 3\text{ V}$ $V_{\text{BBi}} = \overline{V_{\text{BBi}}} = 2.5\text{ V}$	N_{FL}		-137 -143		dBm/Hz
Power-down mode						
Supply current	$V_{\text{PD}} \leq 0.5\text{ V}$, Pins 6, 7, $V_{\text{PD}} = 1\text{ V}$	I_{PD}		10	1	μA
Settling time	Pins 1 to 4 $C_{\text{SPD}} = 100\text{ pF}$ $C_{\text{LO}} = 100\text{ pF}$, $C_{\text{RFo}} = 1\text{ nF}$	t_{SPD}		10		μs
Switching voltage Pin 1						
Power on		V_{PDon}	4			V
Power down		V_{PDdown}			1	V
Reference voltage Pin 13						
Voltage range		V_{Ref}		$2.5 \pm 5\%$		V
Output impedance		Z_{ORef}		30		Ω

Note: ¹ Required LO level is a function of the LO frequency.

Note: ² The LO input impedance is consisting of a 50 Ω resistor in series with a 15 pF capacitor

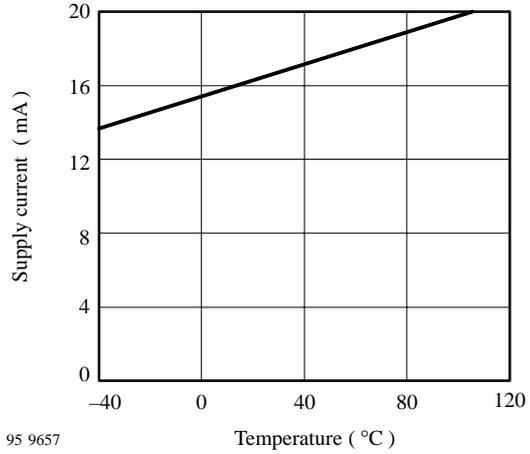
Note: ³ With the Pins 19 and 20 spurious performance especially for low frequency application can be improved by adding a chip capacitor between LP1 and LP2. In conjunction with a parallel resistor the output level can be adjusted to the following mixer stage without degradation of LO suppression and noise performance

Note: 4 which would decrease if the I/Q input level is reduced.
 For $T_{amb} = -40$ to $+85^{\circ}\text{C}$ and $V_S = 4.5$ to 5.5 V



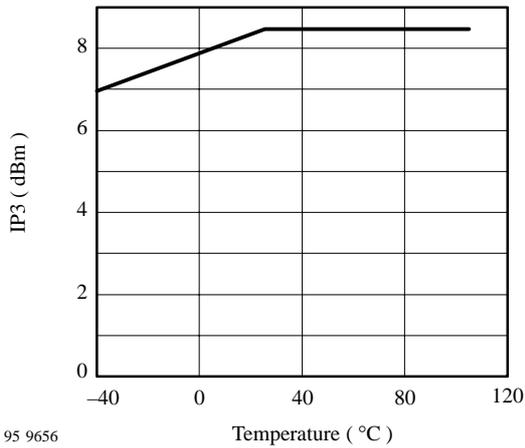
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Figure 3. Reference voltage versus T_{amb}



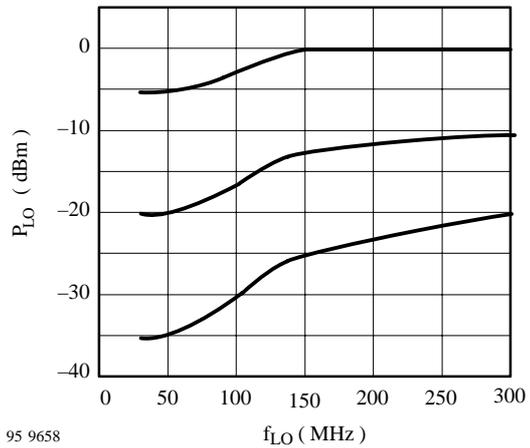
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Figure 5. Supply current versus T_{amb}



95 9656

Figure 4. OIP3 versus T_{amb} , LO = 150 MHz, level -10 dBm



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Figure 6. Recommended LO power range versus LO frequency at $T_{amb} = 25^{\circ}\text{C}$

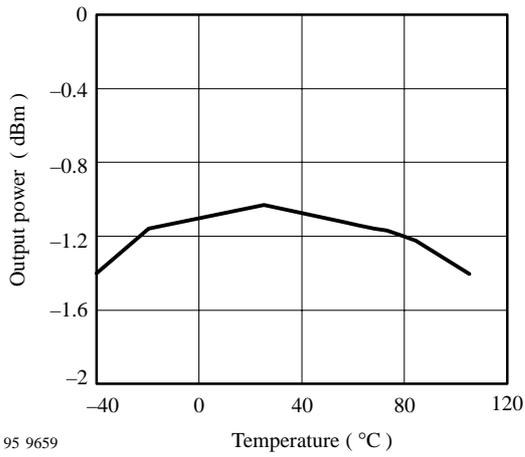


Figure 7. Output power versus T_{amb}

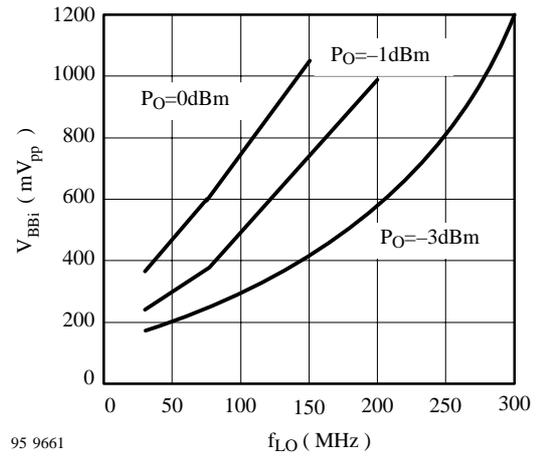


Figure 9. Typical required V_{BBi} input signal (differential) versus LO frequency for $P_O = 1$ dBm and $P_O = -3$ dBm

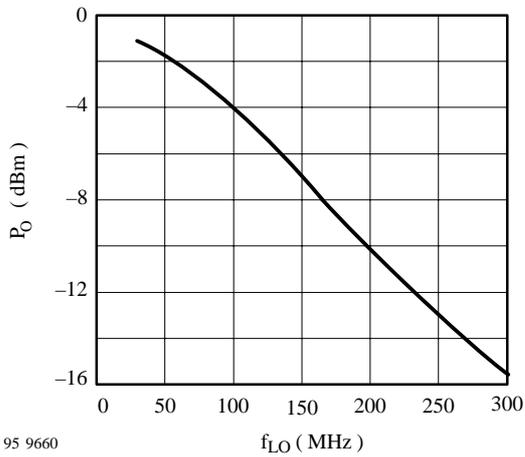
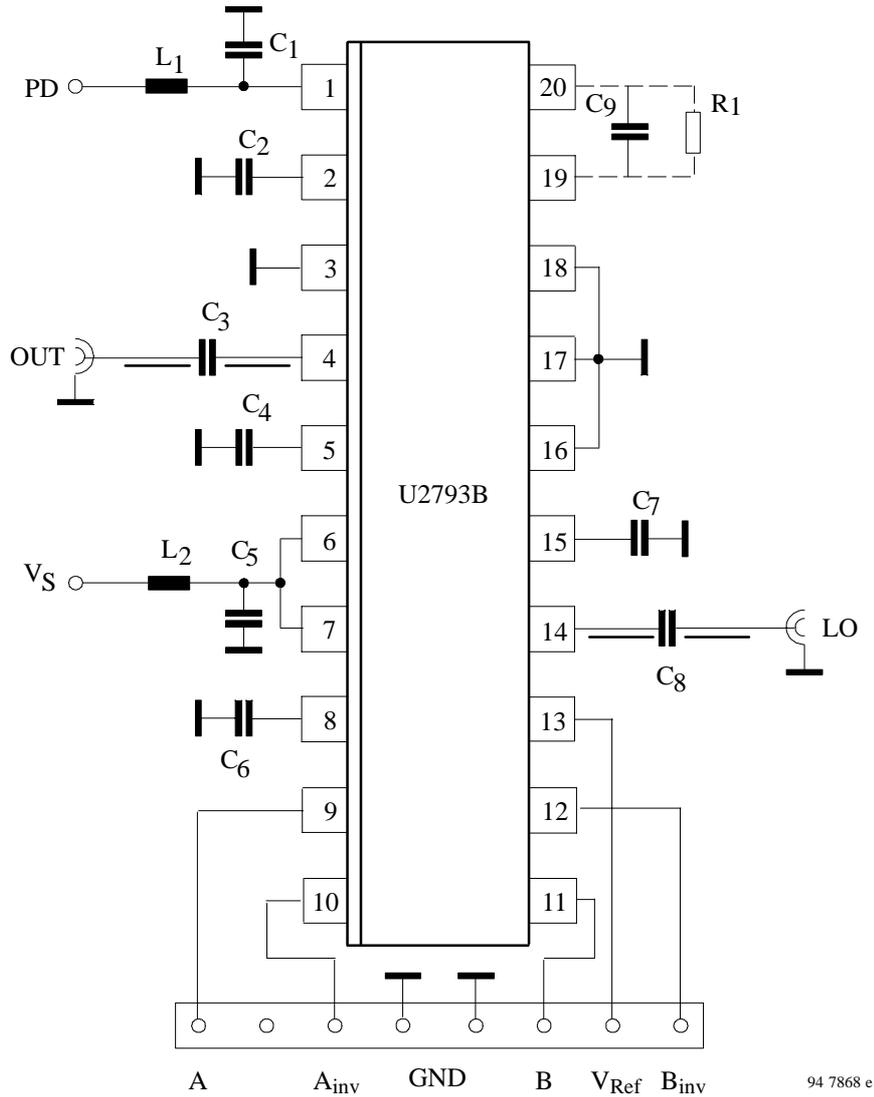


Figure 8. Typical output power vs. LO frequency at $T_{amb} = 25^\circ\text{C}$, $V_{BBi} = 250$ mV (differential)

Evaluation Board Circuitry



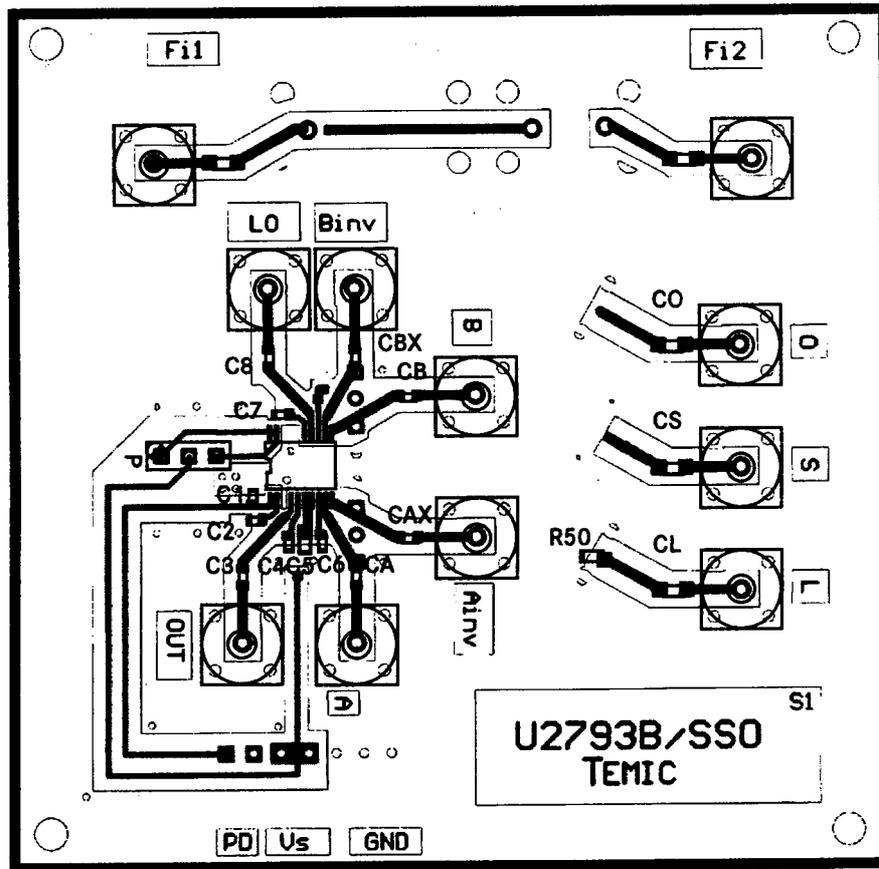
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Figure 10. Evaluation board circuitry

Part list	
C1, C2, C3, C4, C6	1 nF
C7, C8	100 pF
C5	100 nF
C9, R1	1 to 10 pF
L1, L2	PCB Inductor
	50-Ω Microstrip
	optional

The above listed components result in a PD settling time of $< 20 \mu\text{s}$. Use of other component values will require consideration for time requirements in burst-mode applications.

PCB Layout Evaluation Board



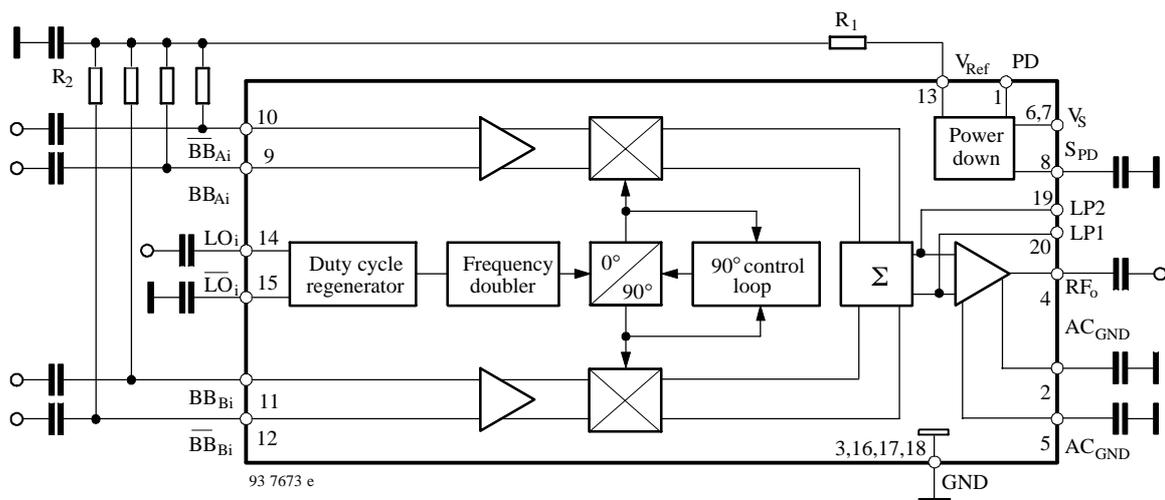
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Figure 11. PCB layout

Application Circuit

Bias network for AC-coupled baseband inputs (V_{BA} , V_{BB}).

$R_1 = 2.5 \text{ k}\Omega$, $R_2 \leq 10 \text{ k}\Omega$ for $\geq 35 \text{ dB}$ LO suppression which is in reference to $< 2 \text{ mV}$ input offset.



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Figure 12. Application circuit with AC-coupled baseband inputs

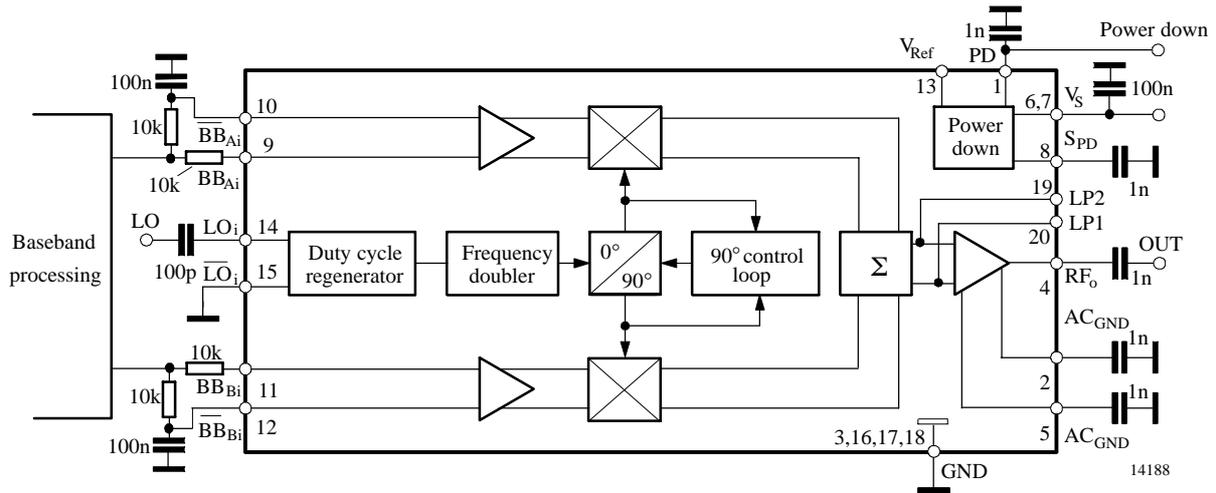
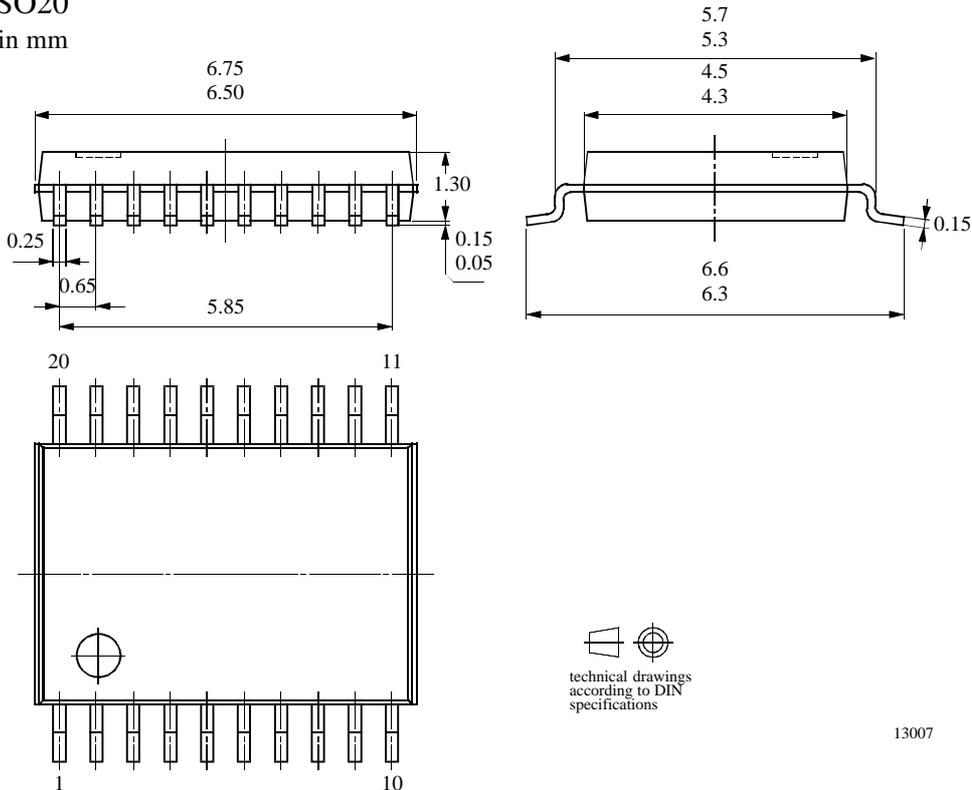


Figure 13. Application circuit with DC-coupled baseband inputs

Package Information

Package SSO20
Dimensions in mm



13007

Ozone Depleting Substances Policy Statement

It is the policy of **Atmel Germany GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Atmel Germany GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Atmel Germany GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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Data sheets can also be retrieved from the Internet: <http://www.atmel-wm.com>

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